GENERAL SEMICONDUCTOR®

1N5711 and 1N6263

Schottky Diodes

DO-204AH (DO-35 Glass)

min. 1.083 (27.5)

max. .150 (3.8)

max. ∅.079 (2.0)

Cathode Mark

Dimensions in inches and (millimeters)

min. 1.083 (27.5)

max. ∅.020 (0.52)
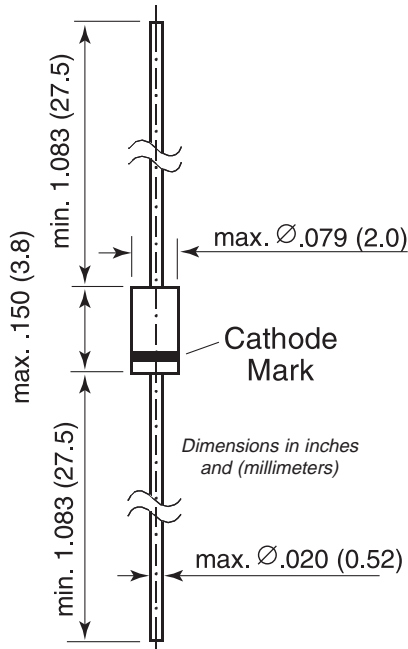
Features

- For general purpose applications
- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.
- This diode is also available in the MiniMELF case with type designation LL5711 and LL6263.

Mechanical Data

Case: DO-35 Glass Case
Weight: approx. 0.13g
Packaging Codes/Options:
   D7/10K per 13" reel (52mm tape), 20K/box
   D8/10K per Ammo tape (52mm tape), 20K/box

Maximum Ratings & Thermal Characteristics
Ratings at 25°C ambient temperature unless otherwise specified.

Parameter		Symbol	Value	Unit
Peak Inverse Voltage	1N5711 1N6263	V_{RRM}	70 60	V
Power Dissipation (Infinite Heatsink)		P_{tot}	400[1]	mW
Maximum Single Cycle Surge 10 μs Square Wave		I_{FSM}	2.0	A
Thermal Resistance Junction to Ambient Air		$R_{\Theta JA}$	0.3[1]	°C/mW
Junction Temperature		T_j	125[1]	°C
Storage Temperature Range		T_S	−55 to +150[1]	°C

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	1N5711 1N6263	$V_{(BR)R}$	I_R = 10μA	70 60	— —	— —	V
Leakage Current		I_R	V_R = 50V	—	—	200	nA
Forward Voltage Drop		V_F	I_F = 1mA I_F = 15mA	— —	— —	0.41 1.0	V
Junction Capacitance		C_{tot}	V_R = 0V, f = 1MHz	—	—	2.2	pF
Reverse Recovery Time		t_{rr}	I_F = I_R = 5mA, recover to $0.1I_R$	—	—	1	ns

Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

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Ratings and
Characteristic Curves (T_A = 25°C unless otherwise noted)
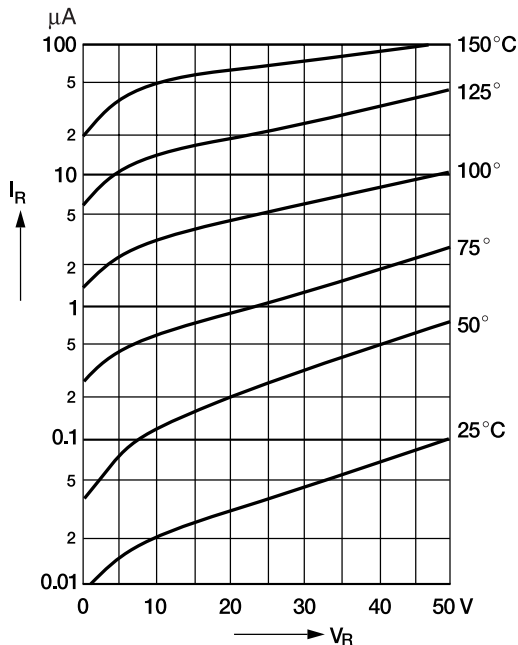
**Typical variation of fwd. current
vs. fwd. voltage for primary conduction
through the Schottky barrier**
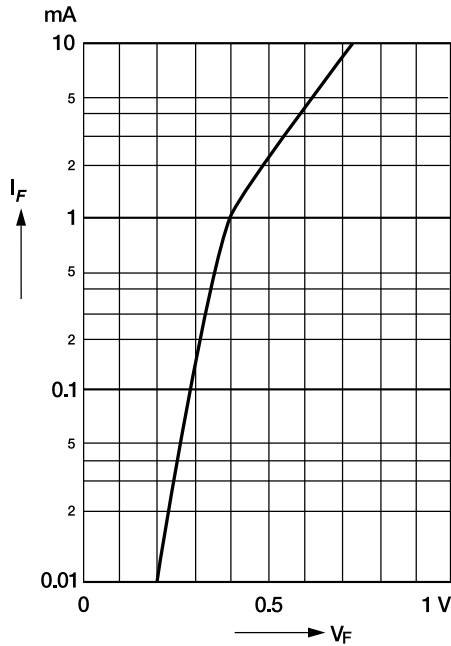
**Typical forward conduction curve
of combination Schottky barrier
and PN junction guard ring**
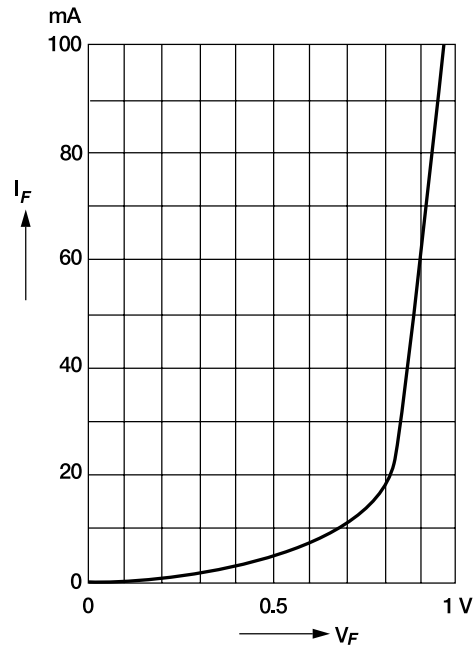
**Typical variation of reverse current
at various temperatures**

**Typical capacitance curve as a
function of reverse voltage**